BSV52LT1G

Switching Transistor

NPN Silicon

Features

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	12	Vdc
Collector - Base Voltage	V _{CBO}	20	Vdc
Collector Current – Continuous	Ic	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

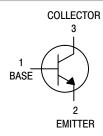
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



B2 = Device Code

M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)

Date Code orientation and/or overbar ma

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]		
BSV52LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BSV52LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

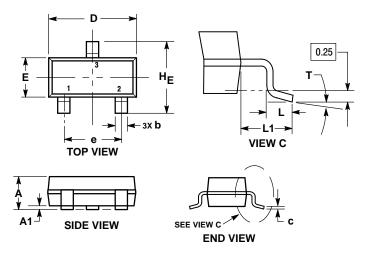
Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 1.0 mAdc)	V _(BR) CEO	12	_	Vdc	
Collector Cutoff Current $(V_{CB} = 10 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 10 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	Ісво	_ _	100 5.0	nAdc μAdc	
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C=1.0 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ &(I_C=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ &(I_C=50 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \end{aligned} $	H _{FE}	25 40 25	- 120 -	-	
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 300 \mu\text{Adc}$) ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}	- - -	300 250 400	mVdc	
Base – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{BE} (sat)	700 -	850 1200	mVdc	
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	400	-	MHz	
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C _{obo}	_	4.0	pF	
Input Capacitance (V _{EB} = 1.0 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	4.5	pF	
SWITCHING CHARACTERISTICS					
Storage Time $(I_C = I_{B1} = I_{B2} = 10 \text{ mAdc})$	t _s	_	13	ns	
Turn–On Time $(V_{BE} = 1.5 \text{ Vdc}, I_C = 10 \text{ mAdc}, I_B = 3.0 \text{ mAdc})$	t _{on}	-	12	ns	
Turn–Off Time (I _C = 10 mAdc, I _B = 3.0 mAdc)	t _{off}	_	18	ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BSV52LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- THE BASE MATERIAL.

 DIMENSIONS O AND E DO NOT INCLUDE MOLD FLASH,

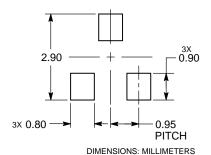
 PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

STYLE 6:

- PIN 1. BASE 2. EMITTER
 - COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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